

Features :

- * 262,144 words by 16 bits organization.
- * Fast access time and cycle time.
- * Dual CAS Input.
- * Low power dissipation.
- * Read-Modify-Write, $\overline{\text{RAS}}$ -Only Refresh, $\overline{\text{CAS}}$ -Before- $\overline{\text{RAS}}$ Refresh, Hidden Refresh and Test Mode Capability.
- * 512 refresh cycles per 8ms.
- * Available in 40-Pin 400 mil SOJ and 40/44 Pin TSOP(II)
- * Single +3.3V±10% Power Supply.
- * All inputs and Outputs are TTL compatible.
- * Extended Data-Out(EDO) Page Mode operation.

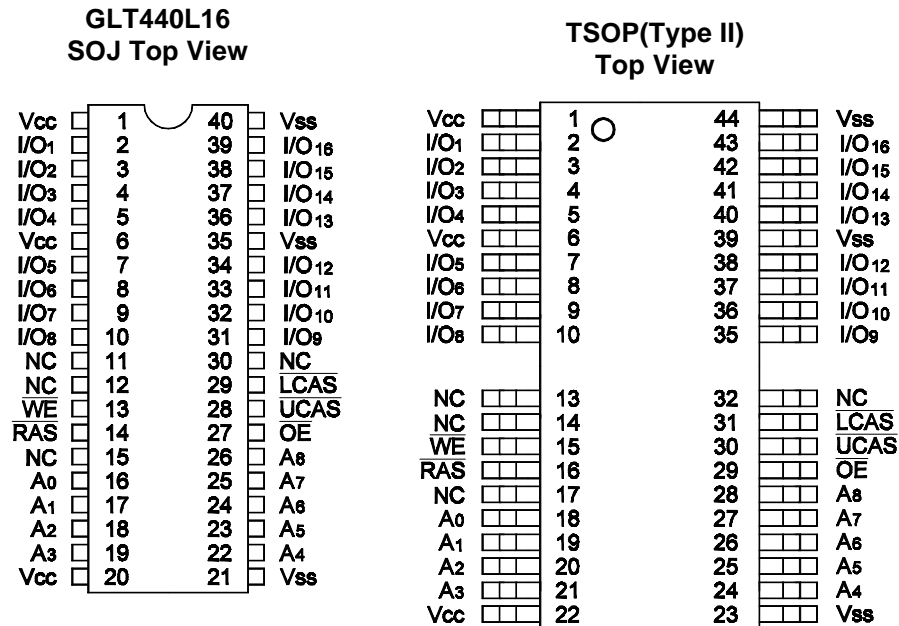
Description :

The GLT440L16 is a 262,144 x 16 bit high-performance CMOS dynamic random access memory. The GLT440L16 offers Fast Page mode with Extended Data Output, and has both BYTE WRITE and WORD WRITE access cycles via two $\overline{\text{CAS}}$ pins. The GLT440L16 has symmetric address and accepts 512-cycle refresh in 8ms interval.

All inputs are TTL compatible. EDO Page Mode operation allows random access up to 512 x 16 bits within a page, with cycle time as short as 14ns.

The GLT440L16 is best suited for graphics, and DSP applications requiring high performance memories.

HIGH PERFORMANCE	35	40	50
Max. $\overline{\text{RAS}}$ Access Time, (t_{RAC})	35 ns	40 ns	50 ns
Max. Column Address Access Time, (t_{CAA})	13 ns	20 ns	25 ns
Min. Extended Data Out Page Mode Cycle Time, (t_{PC})	14 ns	15 ns	19 ns
Min. Read/Write Cycle Time, (t_{RC})	45 ns	75 ns	90 ns
Max. $\overline{\text{CAS}}$ Access Time, (t_{CAC})	11 ns	12 ns	13 ns

Pin Configuration :

Pin Descriptions:

Name	Function
A ₀ - A ₈	Address Inputs
$\overline{\text{RAS}}$	Row Address Strobe
$\overline{\text{UCAS}}$	Column Address Strobe/Upper Byte Control
$\overline{\text{LCAS}}$	Column Address Strobe/Lower Byte Control
$\overline{\text{WE}}$	Write Enable
$\overline{\text{OE}}$	Output Enable
DQ ₁ - DQ ₁₆	Data Inputs / Outputs
V _{CC}	+3.3V Power Supply
V _{SS}	0V Supply
NC	No Connection

Absolute Maximum Ratings*

Operating Temperature, T_A (ambient)
-10°C to +70°C
 Storage Temperature(plastic)....-55°C to +150°C
 Voltage Relative to V_{SS}-1.0V to + 4.6V
 Short Circuit Output Current.....50mA
 Power Dissipation.....1.0W

*Note: Operation above Absolute Maximum Ratings can adversely affect device reliability.

Capacitance*

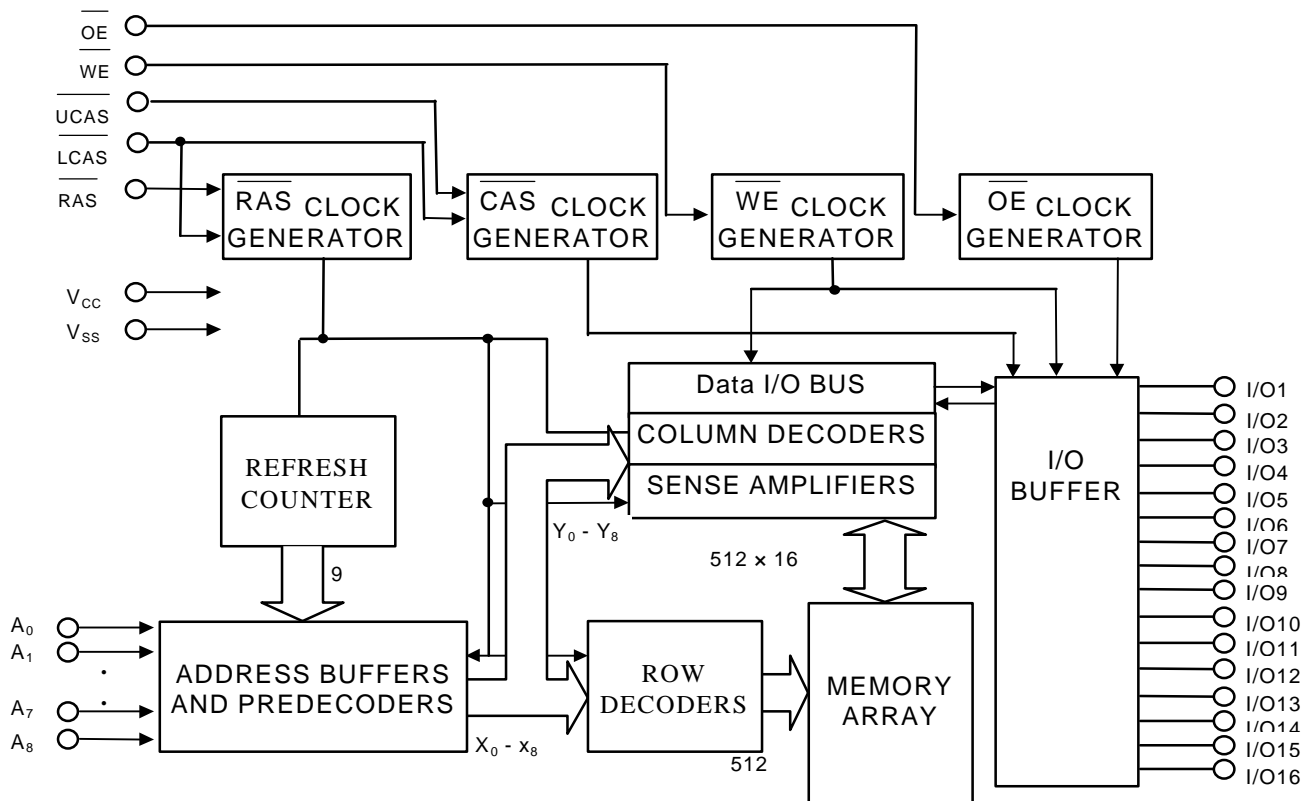
$T_A=25^\circ\text{C}$, $V_{CC}=3.3\text{V}\pm 10\%$, $V_{SS}=0\text{V}$

Symbol	Parameter	Typ	Max.	Unit
C_{IN1}	Address Input	3	4	pF
C_{IN2}	$\overline{\text{RAS}}$, $\overline{\text{LCAS}}$, $\overline{\text{UCAS}}$, $\overline{\text{WE}}$, $\overline{\text{OE}}$	4	5	pF
C_{OUT}	Data Input/Output	5	7	pF

*Note: Capacitance is sampled and not 100% tested

Electrical Specifications

- $\overline{\text{CAS}}$ means $\overline{\text{UCAS}}$ and $\overline{\text{LCAS}}$.
- All voltages are referenced to GND.
- After power up, wait more than 100 μs and then, execute eight $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ or $\overline{\text{RAS}}$ -only refresh cycles as dummy cycles to initialize internal circuit.

Block Diagram :


Truth Table: GLT440L16

Function		$\overline{\text{RAS}}$	$\overline{\text{CASL}}$	$\overline{\text{CASH}}$	$\overline{\text{WE}}$	$\overline{\text{OE}}$	ADDRESS	DQs	Notes
Standby		H	H	H	X	X		High-Z	
Read: Word		L	L	L	H	L	ROW/COL	Data Out	
Read: Lower Byte		L	L	H	H	L	ROW/COL	Lower Byte,Data-Out Upper Byte,High-Z	
Read: Upper Byte		L	H	L	H	L	ROW/COL	Lower Byte,High-Z Upper Byte,Data-Out	
Write: Word(Early Write)		L	L	L	L	X	ROW/COL	Data-In	
Write: Lower Byte (Early)		L	L	H	L	X	ROW/COL	Lower Byte,Data-In Upper Byte,High-Z	
Write: Upper Byte (Early)		L	H	L	L	X	ROW/COL	Lower Byte,High-Z Upper Byte,Data-In	
Read Write		L	L	L	H→L	L→H	ROW/COL	Data-Out,Data-In	1,2
EDO-Page-Mode Read	1st Cycle	L	H→L	H→L	H	L	ROW/COL	Data-Out	2
	2nd Cycle	L	H→L	H→L	H	L	COL	Data-Out	2
EDO-Page-Mode Write	1st Cycle	L	H→L	H→L	L	X	ROW/COL	Data-In	2
	2nd Cycle	L	H→L	H→L	L	X	COL	Data-In	2
EDO-Page-Mode Read-Write	1st Cycle	L	H→L	H→L	H→L	L→H	ROW/COL	Data-Out,Data-In	1,2
	2nd Cycle	L	H→L	H→L	H→L	L→H	COL	Data-Out,Data-In	1,2
Hidden Refresh	Read	L→H→L	L	L	H	L	ROW/COL	Data-Out	2
	Write	L→H→L	L	L	H	L	ROW/COL	Data-In	2
$\overline{\text{RAS}}$ -Only Refresh		L	H	H	X	X	ROW	High-Z	
CBR Refresh		H→L	L	L	X	X		High-Z	3

Notes:

1. These READ cycles may also be BYTE READ cycles (either $\overline{\text{UCAS}}$ or $\overline{\text{LCAS}}$ active).
2. These WRITE cycles may also be BYTE READ cycles (either $\overline{\text{UCAS}}$ or $\overline{\text{LCAS}}$ active).
3. EARLY WRITE only.
4. At least one of the two CAS signals must be active ($\overline{\text{UCAS}}$ or $\overline{\text{LCAS}}$).

DC and Operating Characteristics (1-2)
 $T_A = 0^\circ\text{C to } 70^\circ\text{C}$, $V_{CC} = 3.3\text{V} \pm 10\%$, $V_{SS} = 0\text{V}$, unless otherwise specified.

Sym.	Parameter	Test Conditions	Access Time	Min.	Typ	Max.	Unit	Notes
I_{LI}	Input Leakage Current (any input pin)	$0\text{V} \leq V_{IN} \leq 5.5\text{V}$ (All other pins not under test=0V)		-10		+10	μA	
I_{LO}	Output Leakage Current (for High-Z State)	$0\text{V} \leq V_{out} \leq 5.5\text{V}$ Output is disabled (Hiz)		-10		+10	μA	
I_{CC1}	Operating Current, Random READ/WRITE	$t_{RC} = t_{RC}(\text{min.})$	$t_{RAC} = 35\text{ns}$ $t_{RAC} = 40\text{ns}$ $t_{RAC} = 50\text{ns}$			160 145 125	mA	1,2
I_{CC2}	Standby Current,(TTL)	$\overline{\text{RAS}}$, $\overline{\text{UCAS}}$, $\overline{\text{LCAS}}$ at V_{IH} other inputs $\geq V_{SS}$				4	mA	
I_{CC3}	Refresh Current, RAS-Only	$\overline{\text{RAS}}$ cycling, $\overline{\text{UCAS}}$, $\overline{\text{LCAS}}$ at V_{IH} $t_{RC} = t_{RC}(\text{min.})$	$t_{RAC} = 35\text{ns}$ $t_{RAC} = 40\text{ns}$ $t_{RAC} = 50\text{ns}$			160 145 125	mA	2
I_{CC4}	Operating Current, EDO Page Mode	$\overline{\text{RAS}}$ at V_{IL} , $\overline{\text{UCAS}}$, $\overline{\text{LCAS}}$ address cycling: $t_{PC} = t_{PC}(\text{min.})$	$t_{RAC} = 35\text{ns}$ $t_{RAC} = 40\text{ns}$ $t_{RAC} = 50\text{ns}$			160 145 125	mA	1,2
I_{CC5}	Refresh Current, CAS Before RAS	$\overline{\text{RAS}}$, $\overline{\text{UCAS}}$, $\overline{\text{LCAS}}$ address cycling: $t_{RC} = t_{RC}(\text{min.})$	$t_{RAC} = 35\text{ns}$ $t_{RAC} = 40\text{ns}$ $t_{RAC} = 50\text{ns}$			160 145 125	mA	1
I_{CC6}	Standby Current, (CMOS)	$\overline{\text{RAS}} \geq V_{CC} - 0.2\text{V}$, $\overline{\text{UCAS}} \geq V_{CC} - 0.2\text{V}$, $\overline{\text{LCAS}} \geq V_{CC} - 0.2\text{V}$, All other inputs V_{SS}				1	mA	
V_{CC}	Supply Voltage			3.0		3.6	V	
V_{IL}	Input Low Voltage			-0.3		0.8	V	3
V_{IH}	Input High Voltage			2.0V		$V_{CC} + 0.3$	V	3
V_{OL}	Output Low Voltage	$I_{OL} = 2\text{mA}$				0.4	V	
V_{OH}	Output High Voltage	$I_{OH} = -2\text{mA}$		2.4			V	

Notes:

- I_{CC} is dependent on output loading when the device output is selected. Specified $I_{CC}(\text{max.})$ is measured with the output open.
- I_{CC} is dependent upon the number of address transitions specified $I_{CC}(\text{max.})$ is measured with a maximum of one transition per address cycle in random Read/Write and EDO Fast Page Mode.
- Specified $V_{IL}(\text{min.})$ is steady state operation. During transitions $V_{IL}(\text{min.})$ may undershoot to -0.3V for a period not to exceed 20ns. All AC parameters are measured with $V_{IL}(\text{min.}) \geq V_{SS}$ and $V_{IH}(\text{max.}) \leq V_{CC}$.

AC Characteristics
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$T_A = 0^\circ\text{C to } 70^\circ\text{C}$, $V_{CC} = 3.3\text{ V} \pm 10\%$ $V_{IH}/V_{IL} = 2.0/0.8\text{V}$, $V_{OH}/V_{OL} = 2.0/0.8\text{V}$

 An initial pause of 100 μs and 8 CAS -before-RAS or RAS-only refresh cycles are required after power-up.

Parameter	Symbol	35		40		50		Unit	Notes
		Min.	Max.	Min.	Max.	Min.	Max.		
Read or Write Cycle Time	t_{RC}	70		75		90		ns	
Read Modify write Cycle Time	t_{RWC}	90		93		109		ns	
RAS Precharge Time	t_{RP}	25		25		30		ns	
RAS Pulse Width	t_{RAS}	35	75k	40	100k	50	100k	ns	
Access Time from RAS	t_{RAC}		35		40		50	ns	1,2,3
Access Time from CAS	t_{CAC}		11		12		13	ns	1,5,10
Access Time from Column Address	t_{AA}		18		20		25	ns	1,5,6
CAS to Output Low-Z	t_{CLZ}	0		0		0		ns	
CAS to Output High-Z	t_{CEZ}	3	8	3	8	3	8	ns	
RAS Hold Time	t_{RSH}	10		12		14		ns	
RAS Hold Time Referenced to OE	t_{ROH}	7		8		9		ns	
CAS Hold Time	t_{CSH}	34		34		45		ns	
CAS Pulse width	t_{CAS}	6		6		8		ns	
RAS to CAS Delay Time	t_{RCD}	13	24	18	28	19	37	ns	
RAS to Column Address Delay Time	t_{RAD}	10	17	13	20	14	25	ns	7
CAS to RAS Precharge Time	t_{CRP}	5		5		5		ns	
Row Address Set-Up Time	t_{ASR}	0		0		0		ns	
Row Address Hold Time	t_{RAH}	6		8		9		ns	
Column Address Set-Up Time	t_{ASC}	0		0		0		ns	
Column Address Hold Time	t_{CAH}	5		6		7		ns	
Column Address to RAS Lead Time	t_{RAL}	18		20		25		ns	
Column Address Hold Time Referenced to RAS	t_{AR}	25		34		44		ns	
Read Command Set-Up Time	t_{RCS}	0		0		0		ns	
Read Command Hold Time Referenced to CAS	t_{RCH}	0		0		0		ns	4
Read Command Hold Time Referenced to RAS	t_{RRH}	0		0		0		ns	4
Write Command Set-Up Time	t_{WCS}	0		0		0		ns	8,9
Write Command Hold Time	t_{WCH}	5		6		7		ns	
Write Command Pulse Width	t_{WCP}	5		6		7		ns	
Write Command to RAS Lead Time	t_{RWL}	10		12		13		ns	

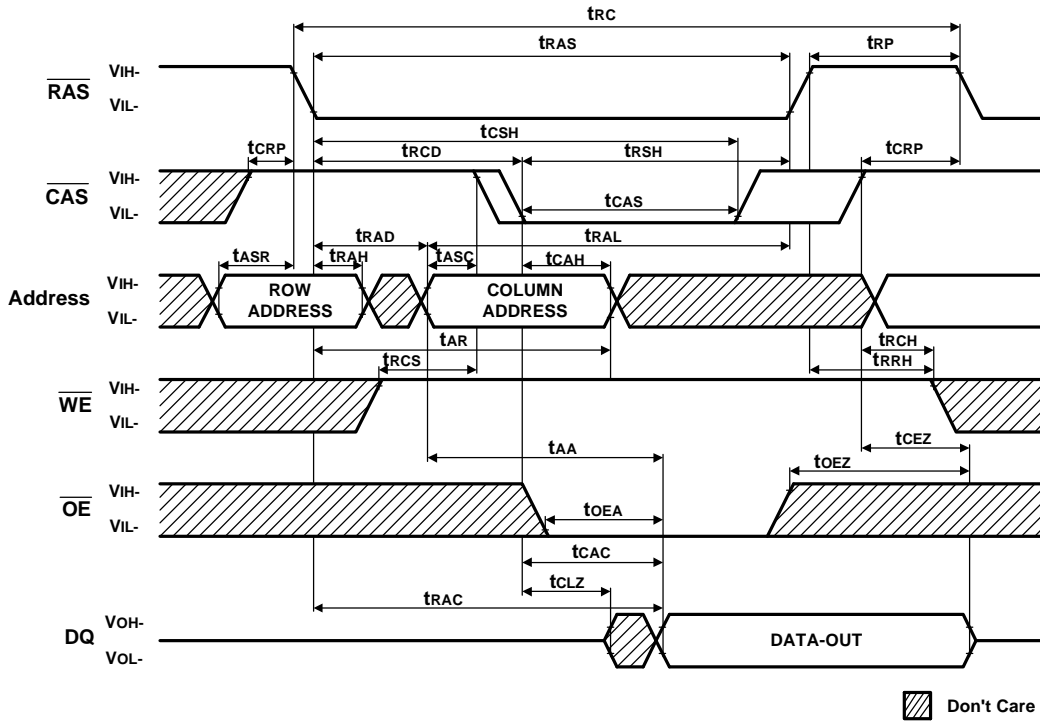
AC Characteristics

Parameter	Symbol	35		40		50		Unit	Notes
		Min.	Max.	Min.	Max.	Min.	Max.		
Write Command to $\overline{\text{CAS}}$ Lead Time	t_{CWL}	8		12		13		ns	
Data Set-Up Time	t_{DS}	0		0		0		ns	
Data Hold Time	t_{DH}	5		8		9		ns	
Data Hold Time Referenced to $\overline{\text{RAS}}$	t_{DHR}	25		36		46		ns	
$\overline{\text{RAS}}$ to $\overline{\text{WE}}$ Delay Time	t_{RWD}	46		54		64		ns	
$\overline{\text{CAS}}$ to $\overline{\text{WE}}$ Delay Time	t_{CWD}	23		24		25		ns	
Column Address to $\overline{\text{WE}}$ Delay Time	t_{AWD}	29		32		37		ns	
$\overline{\text{RAS}}$ to $\overline{\text{CAS}}$ Precharge Time	t_{RPC}	0		0		0		ns	
Access Time from $\overline{\text{CAS}}$ Precharge	t_{CPA}		20		22		30	ns	
EDO Page Mode Cycle Time	t_{PC}	14		15		20		ns	
EDO Page Mode Read-Modify-write Cycle Time	t_{PRWC}	45		50		59		ns	
$\overline{\text{CAS}}$ Precharge Time (EDO Page Mode)	t_{CP}	4		5		8		ns	
$\overline{\text{RAS}}$ Pulse Width (EDO Page Mode Only)	t_{RASP}	35	100k	40	100k	50	100k	ns	
Access Time from $\overline{\text{OE}}$	t_{OEA}		11		12		13	ns	
$\overline{\text{OE}}$ to Data Delay Time	t_{OED}	5		8		8		ns	
$\overline{\text{OE}}$ to Output High-Z	t_{OEZ}	3	8	3	8	3	8	ns	
$\overline{\text{OE}}$ Command Hold Time	t_{OEH}	5		7		7		ns	
Data Output Hold after $\overline{\text{CAS}}$ Low	t_{DOH}	3		3		5		ns	
$\overline{\text{RAS}}$ to Output High-Z	t_{REZ}	3	8	3	8	3	8	ns	
$\overline{\text{WE}}$ to Output High-Z	t_{WEZ}	3	10	3	10	3	12	ns	
$\overline{\text{OE}}$ to $\overline{\text{CAS}}$ Hold Time	t_{OCH}	8		8		8		ns	
$\overline{\text{CAS}}$ Hold Time to $\overline{\text{OE}}$	t_{CHO}	8		8		8		ns	
$\overline{\text{OE}}$ Precharge Time	t_{OEP}	8		8		8		ns	
$\overline{\text{CAS}}$ Set-Up Time for $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ Cycle	t_{CSR}	8		10		10		ns	
$\overline{\text{CAS}}$ Hold Time for $\overline{\text{CAS}}$ -before- $\overline{\text{RAS}}$ Cycle	t_{CHR}	8		10		10		ns	
Transition Time	t_{T}	2	50	2	50	2	50	ns	
Refresh Period	t_{REF}		8		8		8	ms	

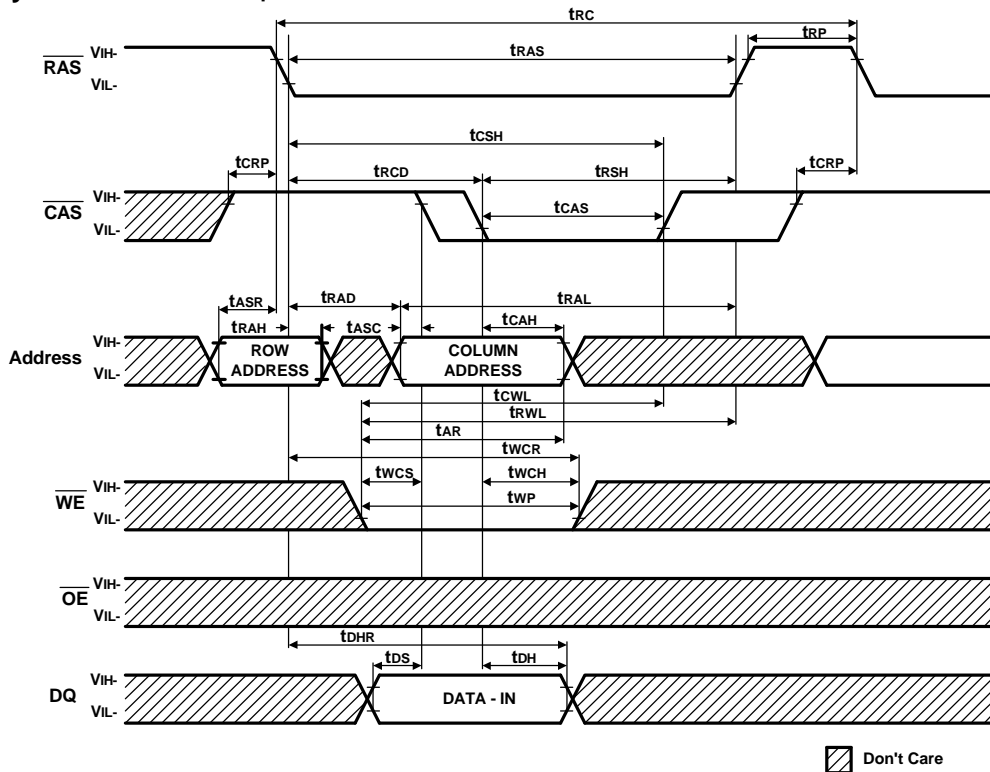
Notes:

1. Measure with a load equivalent to one TTL inputs and 50 pF.
2. Assumes that $t_{RCD} \leq t_{RCD}(\text{max.})$. If t_{RCD} is greater than $t_{RCD}(\text{max.})$, access time will be t_{AA} dominant.
3. Assumes that $t_{RAD} \leq t_{RAD}(\text{max.})$. If t_{RAD} is greater than $t_{RCD}(\text{max.})$, access time will be controlled by t_{CAC} .
4. Either t_{RRH} or t_{RCH} must be satisfied for a Read Cycle.
5. Access time is determined by the longest of t_{CAA} , t_{CAC} and t_{CPA} .
6. Assumes that $t_{RAD} \geq t_{RAD}(\text{max.})$.
7. Operation within the $t_{RAD}(\text{max.})$ limit ensures that $t_{RAC}(\text{max.})$ can be met. $t_{RAD}(\text{max.})$ is specified as a reference point only. If t_{RAD} is greater than the specified $t_{RAD}(\text{max.})$ limit, the access time is controlled by t_{CAA} and t_{CAC} .
8. t_{WCS} , t_{RWD} , t_{AWD} and t_{CWD} are not restrictive operating parameters.
9. $t_{WCS}(\text{min.})$ must be satisfied in an Early Write Cycle.
10. t_{DS} and t_{DH} are referenced to the latter occurrence of $\overline{\text{CAS}}$ of $\overline{\text{WE}}$.
 t_T is measured between $V_{IH}(\text{min.})$ and $V_{IL}(\text{max.})$. AC-measurements assume $t_T = 1.5 \text{ ns}$.

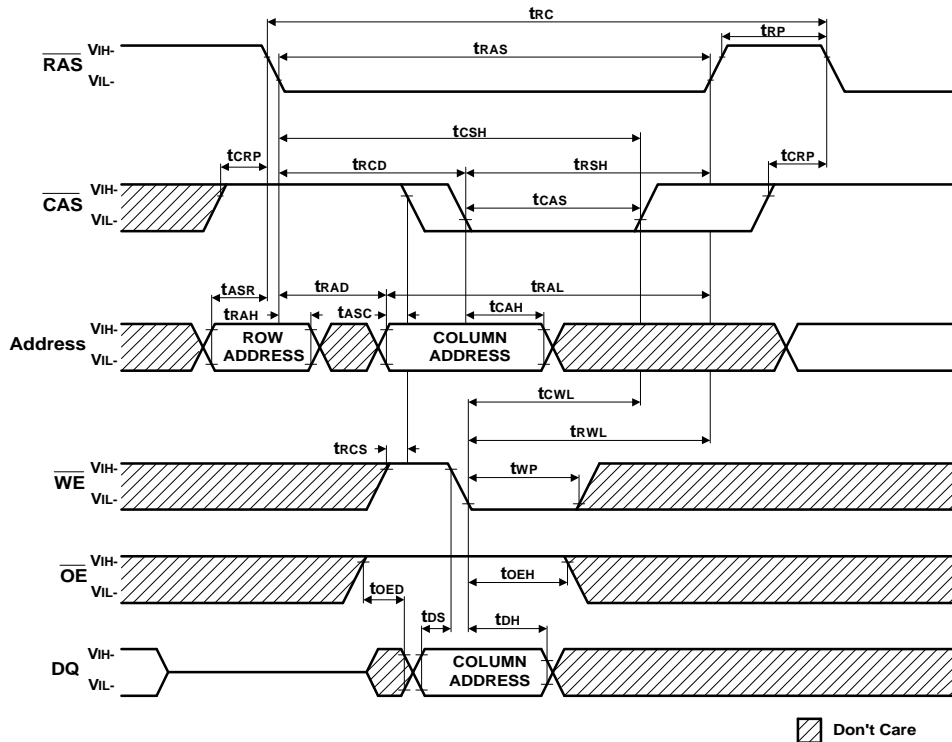
Read Cycle



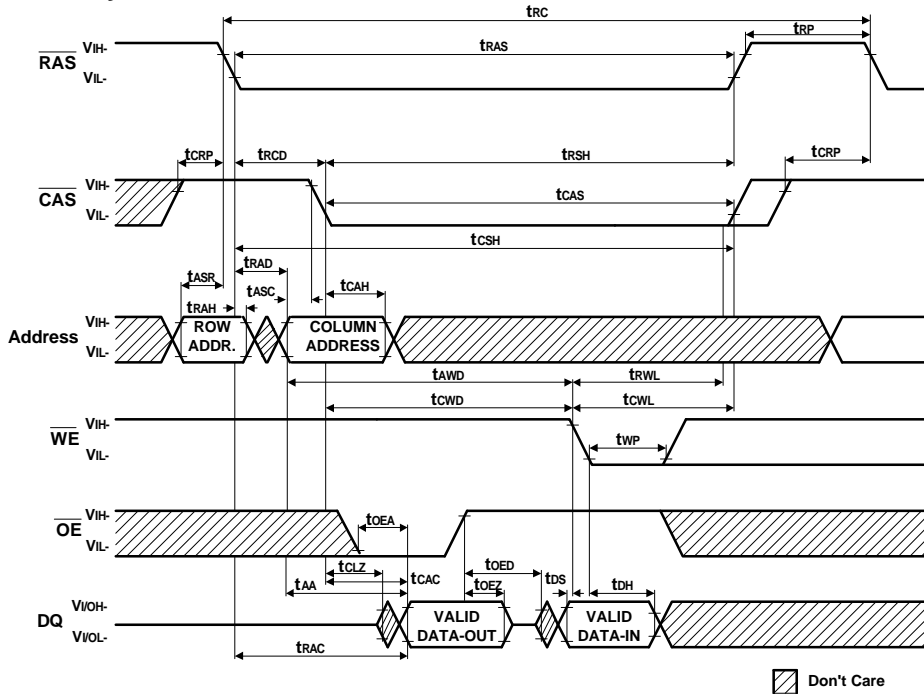
Early Write Cycle NOTE : D_{OUT} = Open

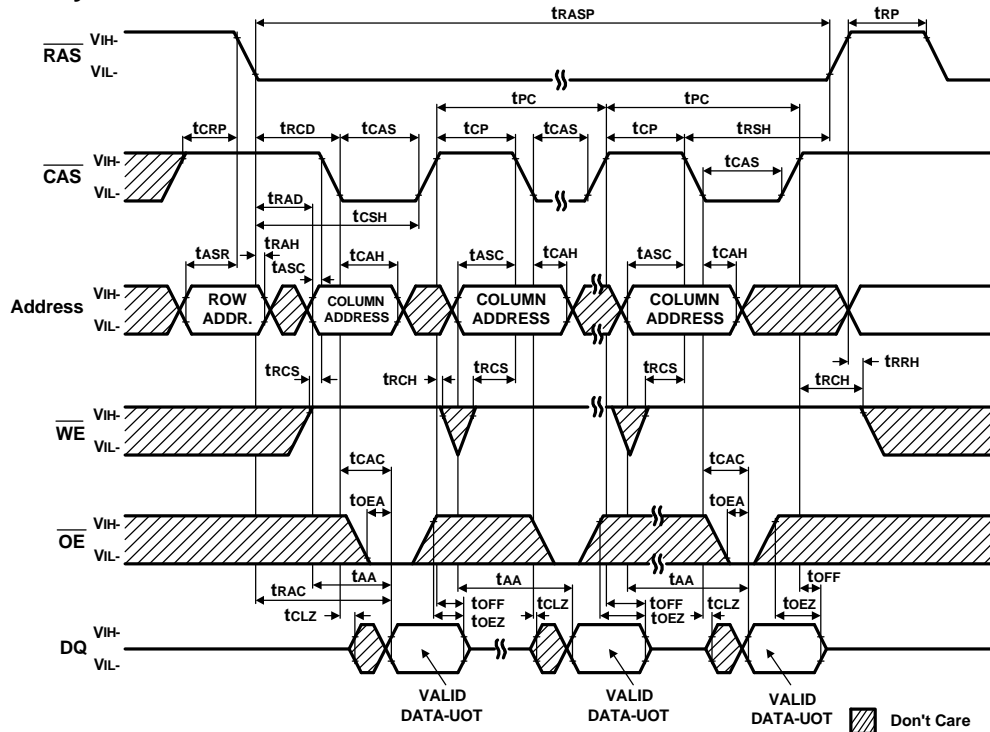
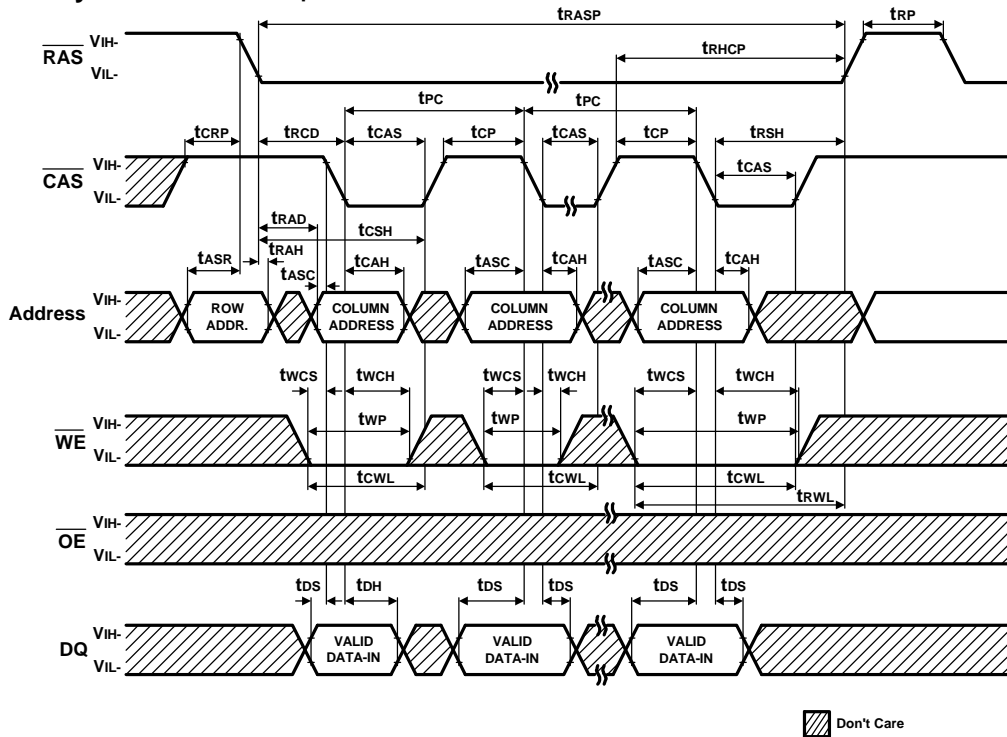


Late Write Cycle (\overline{OE} Controlled Write) NOTE : $D_{OUT} = \text{Open}$

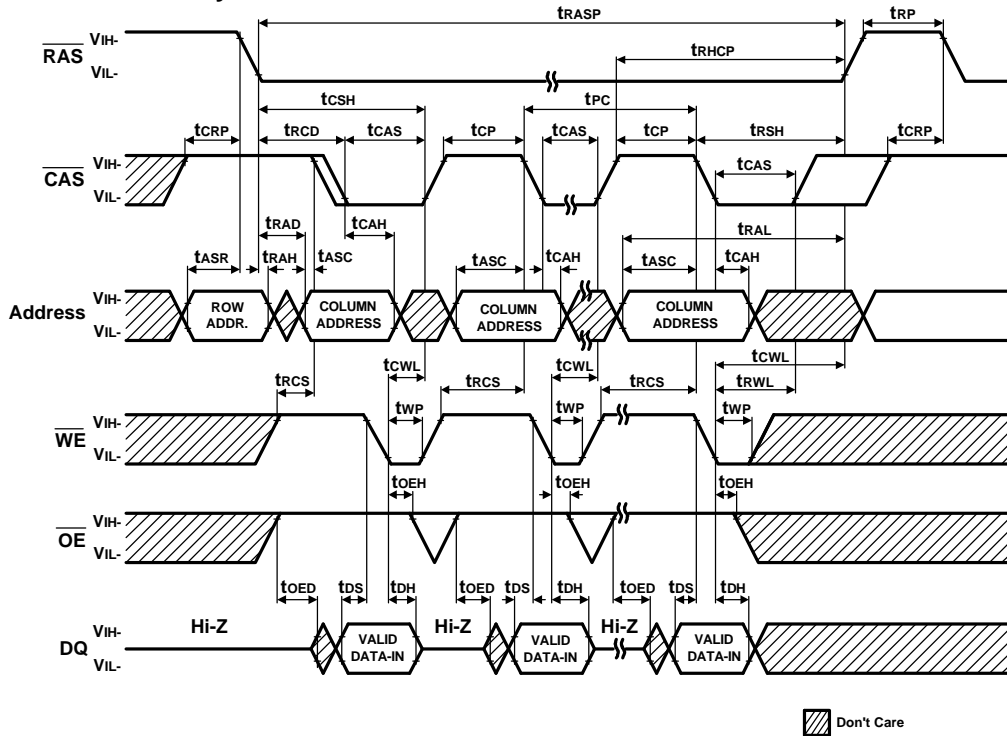


Read - Modify - Write Cycle

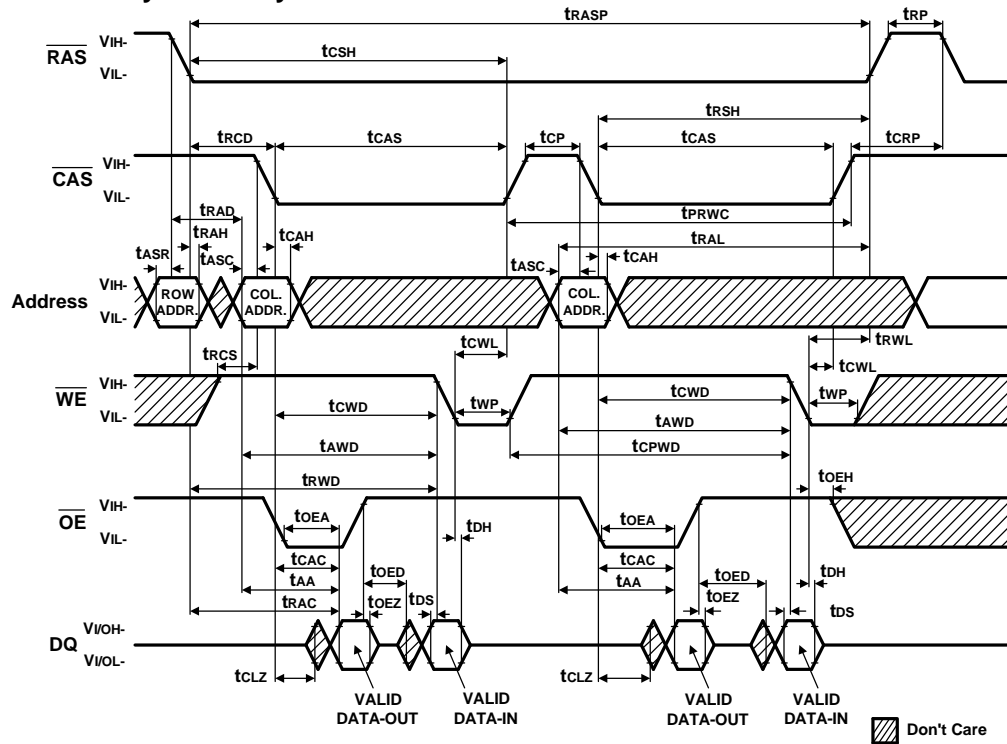


Fast Page Read Cycle

Fast Page Write Cycle NOTE : D_{OUT} = Open


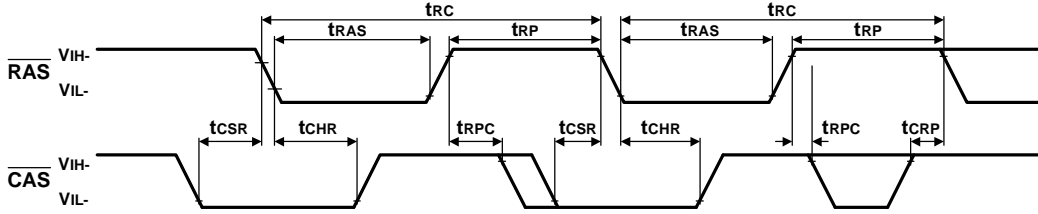
Fast Page Mode Late Write Cycle



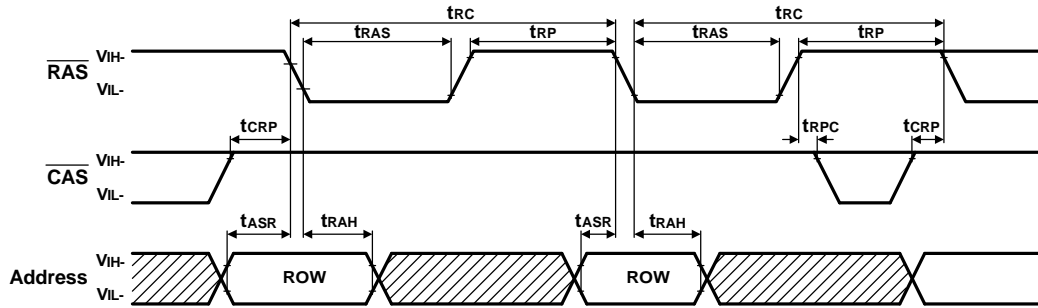
Fast Page Read - Modify - Write Cycle



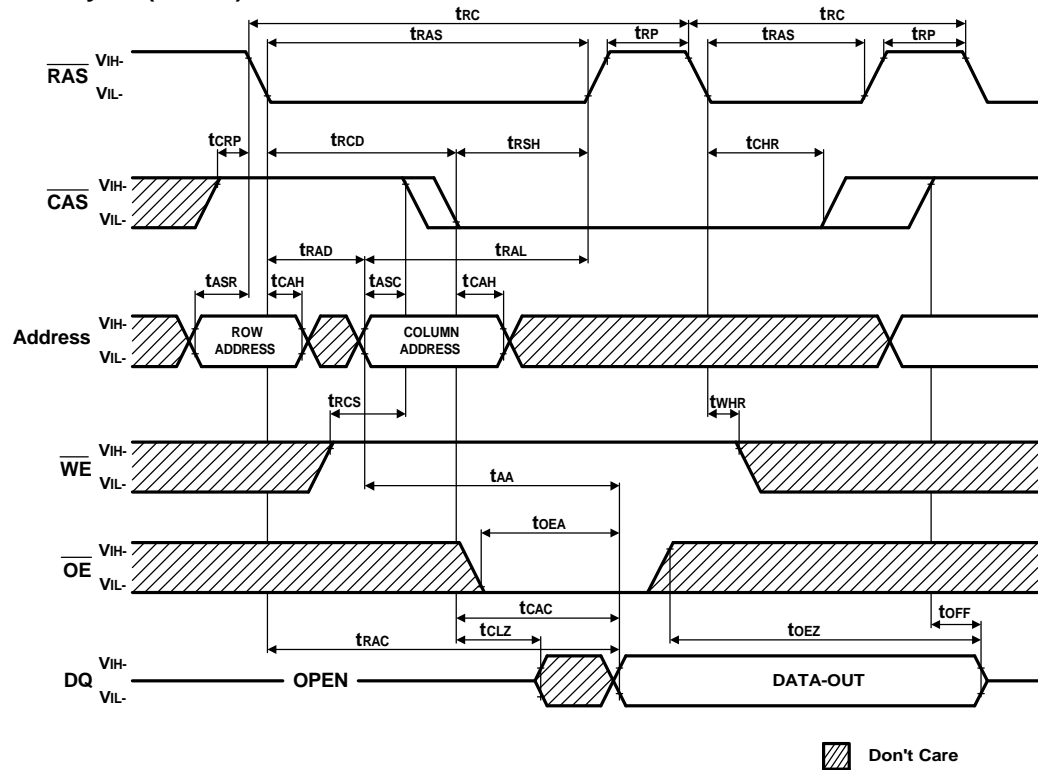
CAS Before RAS Refresh Cycle



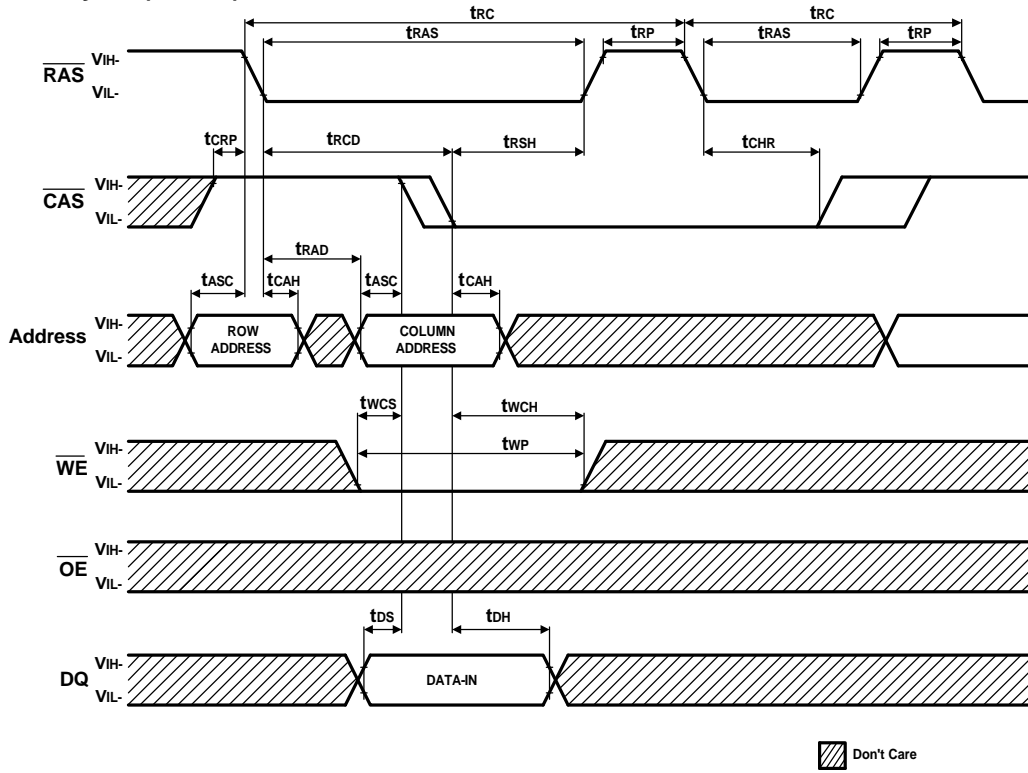
RAS -Only Refresh Cycle



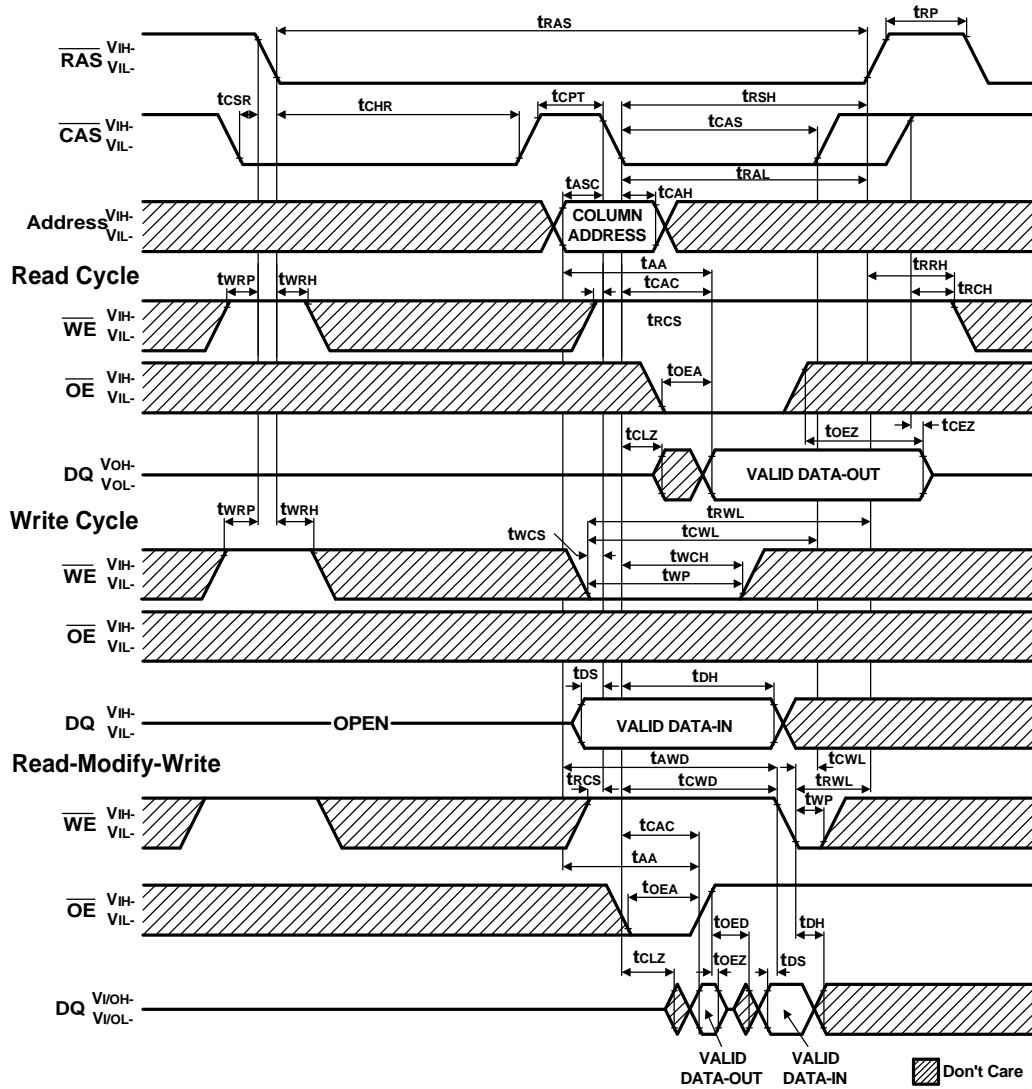
Hidden Refresh Cycle (Read)



Hidden Refresh Cycle (Write) NOTE : D_{OUT} =Open

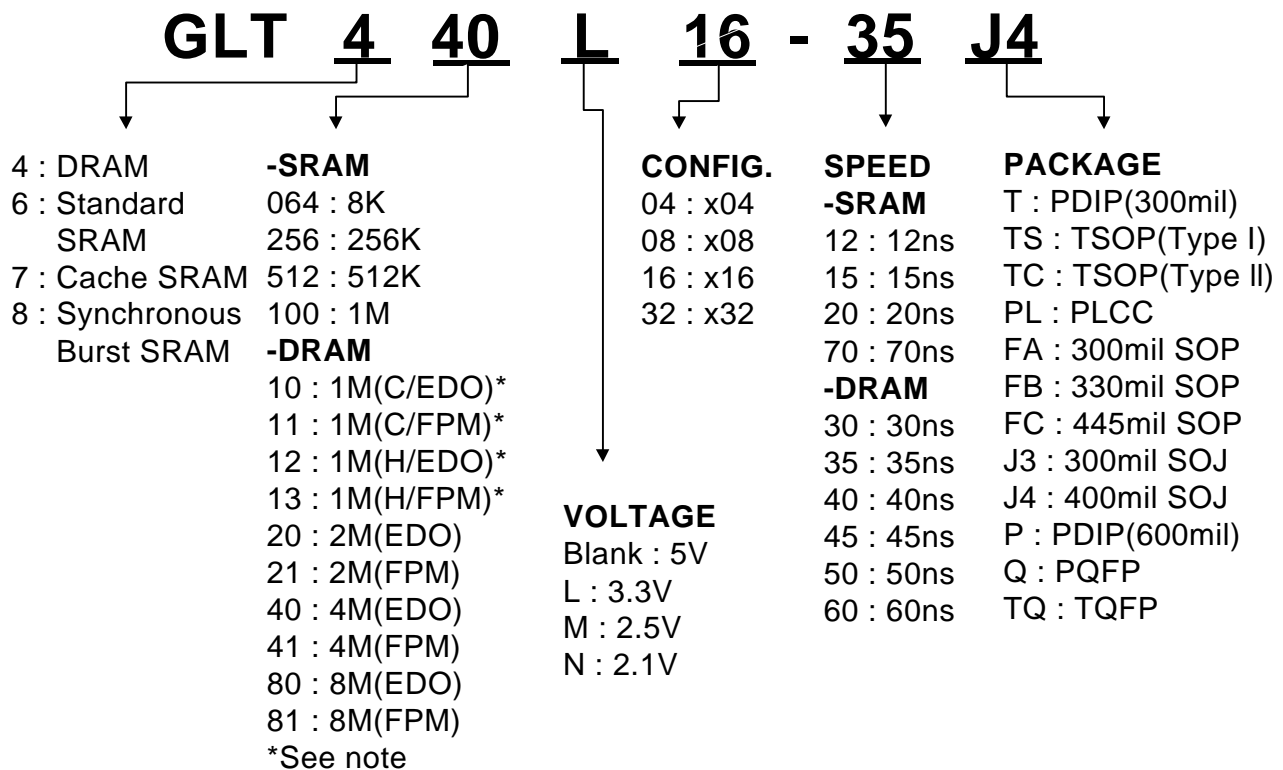


CAS - Before RAS Refresh Counter Test Cycle



Ordering Information

Part Number	SPEED	POWER	FEATURE	PACKAGE
GLT440L16-35J4	35ns	Normal	EDO	40L 400mil SOJ
GLT440L16-40J4	40ns	Normal	EDO	40L 400mil SOJ
GLT440L16-50J4	50ns	Normal	EDO	40L 400mil SOJ
GLT440L16-35TC	35ns	Normal	EDO	44L 400mil TSOP
GLT440L16-40TC	40ns	Normal	EDO	44L 400mil TSOP
GLT440L16-50TC	50ns	Normal	EDO	44L 400mil TSOP

Parts Numbers (Top Mark) Definition :


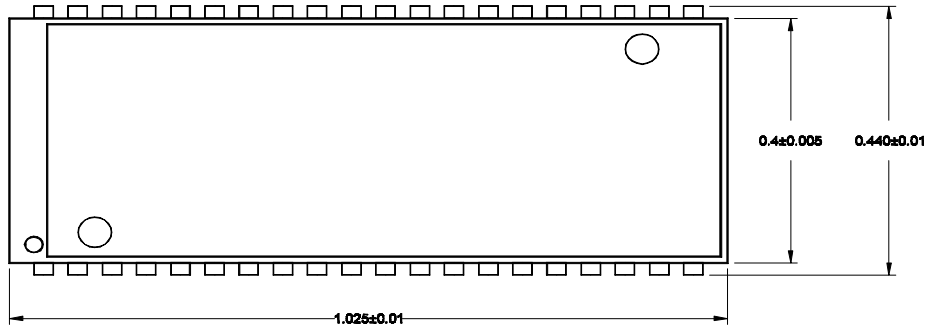
Note : C→CDROM , H→HDD.

Example :

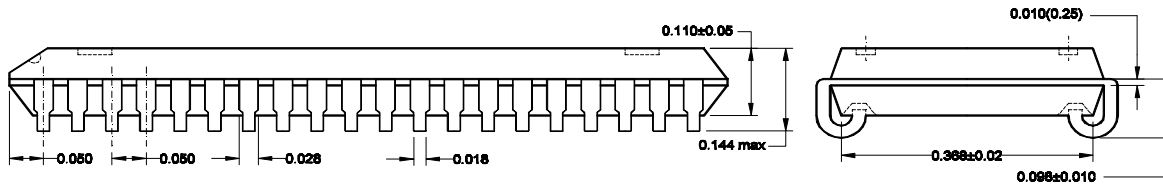
1. GLT710008-15T 1Mbit(128Kx8)15ns 5V SRAM PDIP(300mil)Package type.
2. GLT44016-40J4 4Mbit(256Kx16)40ns 5V DRAM SOJ(400mil)Package type.

Package Information

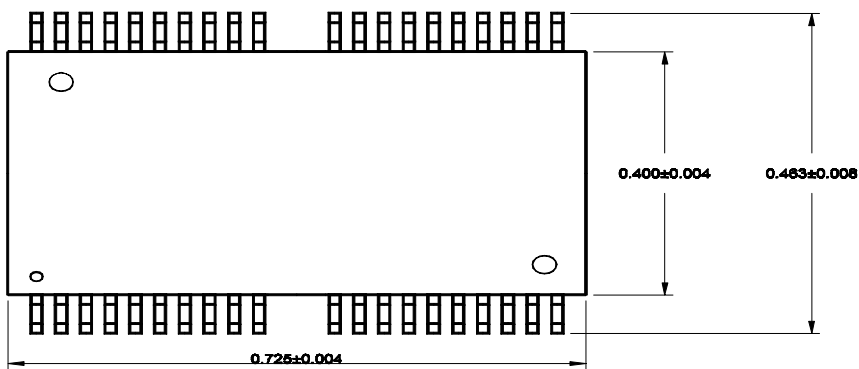
40/44 Lead Thin Small Outline Package SOJ



Unit : Inch



40/44 Lead Thin Small Outline Package TSOP(Type II)



Unit : Inch

